Microchip Technology - AGL030V2-UCG81 Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	768
Total RAM Bits	-
Number of I/O	66
Number of Gates	30000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	81-WFBGA, CSBGA
Supplier Device Package	81-UCSP (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl030v2-ucg81

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

IGLOO Device Family Overview

IGLOO DC and Switching Characteristics

Pin Descriptions

Package Pin Assignments

Datasheet Information

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Microsemi Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-23 on page 2-19.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-24 on page 2-19.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-24 on page 2-19. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

$P_{STAT} = (P_{DC1} \text{ or } P_{DC2} \text{ or } P_{DC3}) + N_{BANKS} * P_{DC5} + N_{INPUTS} * P_{DC6} + N_{OUTPUTS} * P_{DC7}$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

N_{BANKS} is the number of I/O banks powered in the design.

Total Dynamic Power Consumption—P_{DYN}

$P_{DYN} = P_{CLOCK} + P_{S\text{-}CELL} + P_{C\text{-}CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$

Global Clock Contribution—P_{CLOCK}

$P_{CLOCK} = (P_{AC1} + N_{SPINE} * P_{AC2} + N_{ROW} * P_{AC3} + N_{S\text{-}CELL} * P_{AC4}) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the *IGLOO FPGA Fabric User Guide.*

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the *IGLOO FPGA Fabric User Guide.*

F_{CLK} is the global clock signal frequency.

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

P_{AC1}, P_{AC2}, P_{AC3}, and P_{AC4} are device-dependent.

Sequential Cells Contribution—$P_{S\text{-}CELL}$

$P_{S\text{-}CELL} = N_{S\text{-}CELL} * (P_{AC5} + \alpha_1 / 2 * P_{AC6}) * F_{CLK}$

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-23 on page 2-19.

F_{CLK} is the global clock signal frequency.

Table 2-39 • **I/O Output Buffer Maximum Resistances[1]
Applicable to Standard Plus I/O Banks**

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω)[2]	$R_{PULL\text{-}UP}$ (Ω)[3]
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	25	75
3.3 V LVCMOS Wide Range	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
1.2 V LVCMOS[4]	2 mA	158	164
1.2 V LVCMOS Wide Range[4]	100 µA	Same as regular 1.2 V LVCMOS	Same as regular 1.2 V LVCMOS
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. *These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at http://www.microsemi.com/soc/download/ibis/default.aspx.*
2. $R_{(PULL\text{-}DOWN\text{-}MAX)} = (VOLspec) / I_{OLspec}$
3. $R_{(PULL\text{-}UP\text{-}MAX)} = (VCCImax – VOHspec) / I_{OHspec}$
4. *Applicable to IGLOO V2 Devices operating at VCCI ≥ VCC*

Table 2-77 • **3.3 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case V_{CC} = 1.14 V, Worst-Case VCCI = 2.7
Applicable to Standard Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	2 mA	Std.	1.55	6.44	0.26	1.29	1.10	6.44	5.64	2.99	3.28	ns
100 µA	4 mA	Std.	1.55	6.44	0.26	1.29	1.10	6.44	5.64	2.99	3.28	ns
100 µA	6 mA	Std.	1.55	5.41	0.26	1.29	1.10	5.41	4.91	3.35	3.89	ns
100 µA	8 mA	Std.	1.55	5.41	0.26	1.29	1.10	5.41	4.91	3.35	3.89	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-78 • **3.3 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7
Applicable to Standard Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	2 mA	Std.	1.55	3.89	0.26	1.29	1.10	3.89	3.13	2.99	3.45	ns
100 µA	4 mA	Std.	1.55	3.89	0.26	1.29	1.10	3.89	3.13	2.99	3.45	ns
100 µA	6 mA	Std.	1.55	3.33	0.26	1.29	1.10	3.33	2.62	3.34	4.07	ns
100 µA	8 mA	Std.	1.55	3.33	0.26	1.29	1.10	3.33	2.62	3.34	4.07	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*
3. *Software default selection highlighted in gray.*

Table 2-97 • Minimum and Maximum DC Input and Output Levels Applicable to Standard I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	**Min. V**	**Max. V**	**Min. V**	**Max. V**	**Max. V**	**Min. V**	**mA**	**mA**	**Max. mA[3]**	**Max. mA[3]**	**µA[4]**	**µA[4]**
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	2	2	9	11	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4	17	22	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

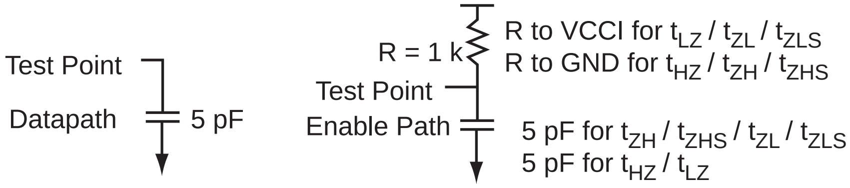

Figure 2-9 • AC Loading

Table 2-98 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	1.8	0.9	5

*Note: *Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.*

Timing Characteristics

1.5 V DC Core Voltage

Table 2-99 • 1.8 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	6.38	0.18	1.01	0.66	6.51	5.93	2.33	1.56	10.10	9.53	ns
4 mA	Std.	0.97	5.35	0.18	1.01	0.66	5.46	5.04	2.67	2.38	9.05	8.64	ns
6 mA	Std.	0.97	4.62	0.18	1.01	0.66	4.71	4.44	2.90	2.79	8.31	8.04	ns
8 mA	Std.	0.97	4.37	0.18	1.01	0.66	4.46	4.31	2.95	2.89	8.05	7.90	ns
12 mA	Std.	0.97	4.32	0.18	1.01	0.66	4.37	4.32	3.03	3.30	7.97	7.92	ns
16 mA	Std.	0.97	4.32	0.18	1.01	0.66	4.37	4.32	3.03	3.30	7.97	7.92	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

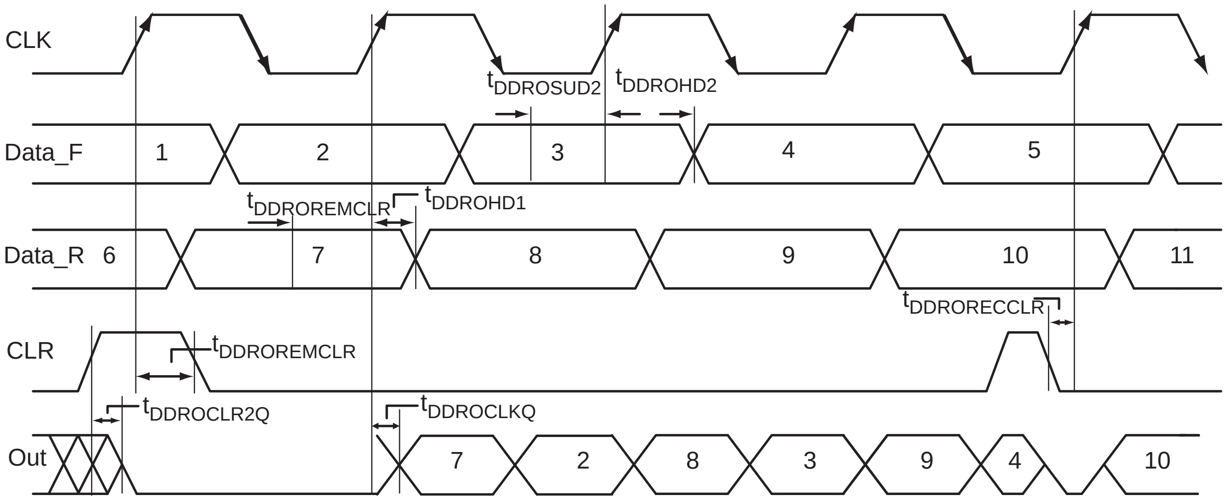

Figure 2-24 • **Output DDR Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-167 • **Output DDR Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
$t_{DDROCLKQ}$	Clock-to-Out of DDR for Output DDR	1.07	ns
$t_{DDROSUD1}$	Data_F Data Setup for Output DDR	0.67	ns
$t_{DDROSUD2}$	Data_R Data Setup for Output DDR	0.67	ns
$t_{DDROHD1}$	Data_F Data Hold for Output DDR	0.00	ns
$t_{DDROHD2}$	Data_R Data Hold for Output DDR	0.00	ns
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out for Output DDR	1.38	ns
$t_{DDROREMCLR}$	Asynchronous Clear Removal Time for Output DDR	0.00	ns
$t_{DDRORECCLR}$	Asynchronous Clear Recovery Time for Output DDR	0.23	ns
$t_{DDROWCLR1}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.19	ns
$t_{DDROCKMPWH}$	Clock Minimum Pulse Width High for the Output DDR	0.31	ns
$t_{DDROCKMPWL}$	Clock Minimum Pulse Width Low for the Output DDR	0.28	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	250.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

**Table 2-175 • AGL060 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V**

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.33	1.55	ns
t_{RCKH}	Input High Delay for Global Clock	1.35	1.62	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.18		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.27	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

**Table 2-176 • AGL125 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V**

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.36	1.71	ns
t_{RCKH}	Input High Delay for Global Clock	1.39	1.82	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.18		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.43	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Embedded SRAM and FIFO Characteristics

SRAM

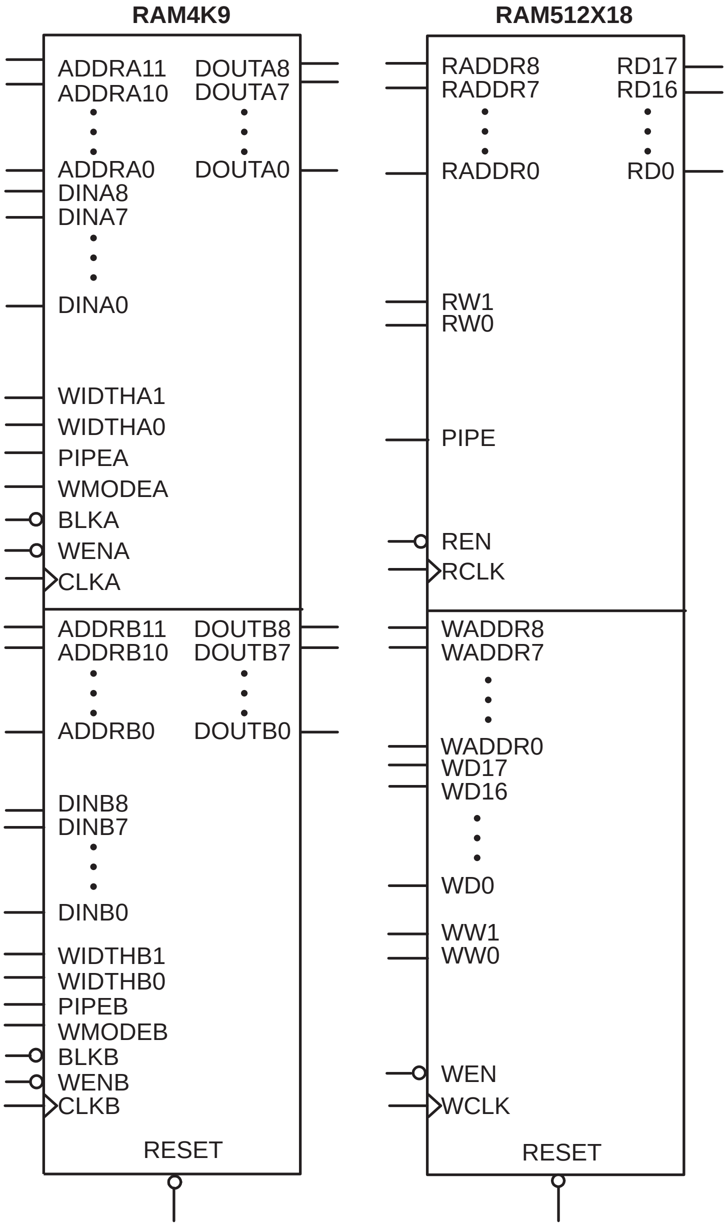

Figure 2-31 • **RAM Models**

Table 2-192 • RAM512X18
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.83	ns
t_{AH}	Address hold time	0.16	ns
t_{ENS}	REN, WEN setup time	0.73	ns
t_{ENH}	REN, WEN hold time	0.08	ns
t_{DS}	Input data (WD) setup time	0.71	ns
t_{DH}	Input data (WD) hold time	0.36	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	4.21	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	1.71	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address - Applicable to Opening Edge	0.35	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address - Applicable to Opening Edge	0.42	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	2.06	ns
	RESET Low to data out Low on RD (pipelined)	2.06	ns
$t_{REMRSTB}$	RESET removal	0.61	ns
$t_{RECRSTB}$	RESET recovery	3.21	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs*.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

CS281	
Pin Number	**AGL600 Function**
R15	IO94RSB2
R16	GDA1/IO88PPB1
R18	GDB0/IO87NPB1
R19	GDC0/IO86NPB1
T1	IO148PPB3
T2	GEC0/IO146NPB3
T4	GEB0/IO145NPB3
T5	IO132RSB2
T6	IO136RSB2
T7	IO130RSB2
T8	IO126RSB2
T9	IO120RSB2
T10	GND
T11	IO113RSB2
T12	IO104RSB2
T13	IO101RSB2
T14	IO98RSB2
T15	GDC2/IO91RSB2
T16	TMS
T18	VJTAG
T19	GDB1/IO87PPB1
U1	IO147PDB3
U2	GEA1/IO144PPB3
U6	IO131RSB2
U14	IO99RSB2
U18	TRST
U19	GDA0/IO88NPB1
V1	IO147NDB3
V2	VCCIB3
V3	GEC2/IO141RSB2
V4	IO140RSB2
V5	IO135RSB2
V6	GND
V7	IO125RSB2
V8	IO122RSB2
V9	IO116RSB2

CS281	
Pin Number	**AGL600 Function**
V10	IO112RSB2
V11	IO110RSB2
V12	IO108RSB2
V13	IO102RSB2
V14	GND
V15	IO93RSB2
V16	GDA2/IO89RSB2
V17	TDI
V18	VCCIB2
V19	TDO
W1	GND
W2	FF/GEB2/IO142RSB2
W3	IO139RSB2
W4	IO137RSB2
W5	IO134RSB2
W6	IO133RSB2
W7	IO128RSB2
W8	IO124RSB2
W9	IO119RSB2
W10	VCCIB2
W11	IO109RSB2
W12	IO107RSB2
W13	IO105RSB2
W14	IO100RSB2
W15	IO96RSB2
W16	IO92RSB2
W17	GDB2/IO90RSB2
W18	TCK
W19	GND

CS281	
Pin Number	**AGL1000 Function**
R15	IO122RSB2
R16	GDA1/IO113PPB1
R18	GDB0/IO112NPB1
R19	GDC0/IO111NPB1
T1	IO197PPB3
T2	GEC0/IO190NPB3
T4	GEB0/IO189NPB3
T5	IO181RSB2
T6	IO172RSB2
T7	IO171RSB2
T8	IO156RSB2
T9	IO159RSB2
T10	GND
T11	IO139RSB2
T12	IO138RSB2
T13	IO129RSB2
T14	IO123RSB2
T15	GDC2/IO116RSB2
T16	TMS
T18	VJTAG
T19	GDB1/IO112PPB1
U1	IO193PDB3
U2	GEA1/IO188PPB3
U6	IO167RSB2
U14	IO128RSB2
U18	TRST
U19	GDA0/IO113NPB1
V1	IO193NDB3
V2	VCCIB3
V3	GEC2/IO185RSB2
V4	IO182RSB2
V5	IO175RSB2
V6	GND
V7	IO161RSB2
V8	IO143RSB2
V9	IO146RSB2

CS281	
Pin Number	**AGL1000 Function**
V10	IO145RSB2
V11	IO144RSB2
V12	IO134RSB2
V13	IO133RSB2
V14	GND
V15	IO119RSB2
V16	GDA2/IO114RSB2
V17	TDI
V18	VCCIB2
V19	TDO
W1	GND
W2	FF/GEB2/IO186RSB2
W3	IO183RSB2
W4	IO176RSB2
W5	IO170RSB2
W6	IO162RSB2
W7	IO157RSB2
W8	IO152RSB2
W9	IO149RSB2
W10	VCCIB2
W11	IO140RSB2
W12	IO135RSB2
W13	IO130RSB2
W14	IO125RSB2
W15	IO120RSB2
W16	IO118RSB2
W17	GDB2/IO115RSB2
W18	TCK
W19	GND

QN132	
Pin Number	**AGL250 Function**
C17	IO74RSB2
C18	VCCIB2
C19	TCK
C20	VMV2
C21	VPUMP
C22	VJTAG
C23	VCCIB1
C24	IO53NSB1
C25	IO51NPB1
C26	GCA1/IO50PPB1
C27	GCC0/IO48NDB1
C28	VCCIB1
C29	IO42NDB1
C30	GNDQ
C31	GBA1/IO40RSB0
C32	GBB0/IO37RSB0
C33	VCC
C34	IO24RSB0
C35	IO19RSB0
C36	IO16RSB0
C37	IO10RSB0
C38	VCCIB0
C39	GAB1/IO03RSB0
C40	VMV0
D1	GND
D2	GND
D3	GND
D4	GND

FG144	
Pin Number	**AGL400 Function**
K1	GEB0/IO136NDB3
K2	GEA1/IO135PDB3
K3	GEA0/IO135NDB3
K4	GEA2/IO134RSB2
K5	IO127RSB2
K6	IO121RSB2
K7	GND
K8	IO104RSB2
K9	GDC2/IO82RSB2
K10	GND
K11	GDA0/IO79VDB1
K12	GDB0/IO78VDB1
L1	GND
L2	VMV3
L3	FF/GEB2/IO133RSB2
L4	IO128RSB2
L5	VCCIB2
L6	IO119RSB2
L7	IO114RSB2
L8	IO110RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO132RSB2
M3	IO129RSB2
M4	IO126RSB2
M5	IO124RSB2
M6	IO122RSB2
M7	IO117RSB2
M8	IO115RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG256	
Pin Number	**AGL1000 Function**
H3	GFB1/IO208PPB3
H4	VCOMPLF
H5	GFC0/IO209NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO91NPB1
H13	GCB1/IO92PPB1
H14	GCA0/IO93NPB1
H15	IO96NPB1
H16	GCB0/IO92NPB1
J1	GFA2/IO206PSB3
J2	GFA1/IO207PDB3
J3	VCCPLF
J4	IO205NDB3
J5	GFB2/IO205PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO95PPB1
J13	GCA1/IO93PPB1
J14	GCC2/IO96PPB1
J15	IO100PPB1
J16	GCA2/IO94PSB1
K1	GFC2/IO204PDB3
K2	IO204NDB3
K3	IO203NDB3
K4	IO203PDB3
K5	VCCIB3
K6	VCC
K7	GND
K8	GND

FG256	
Pin Number	**AGL1000 Function**
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO95NPB1
K14	IO100NPB1
K15	IO102NDB1
K16	IO102PDB1
L1	IO202NDB3
L2	IO202PDB3
L3	IO196PPB3
L4	IO193PPB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO112NPB1
L14	IO106NDB1
L15	IO106PDB1
L16	IO107PDB1
M1	IO197NSB3
M2	IO196NPB3
M3	IO193NPB3
M4	GEC0/IO190NPB3
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO147RSB2
M9	IO136RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO110NDB1
M14	GDB1/IO112PPB1

FG256	
Pin Number	**AGL1000 Function**
M15	GDC1/IO111PDB1
M16	IO107NDB1
N1	IO194PSB3
N2	IO192PPB3
N3	GEC1/IO190PPB3
N4	IO192NPB3
N5	GNDQ
N6	GEA2/IO187RSB2
N7	IO161RSB2
N8	IO155RSB2
N9	IO141RSB2
N10	IO129RSB2
N11	IO124RSB2
N12	GNDQ
N13	IO110PDB1
N14	VJTAG
N15	GDC0/IO111NDB1
N16	GDA1/IO113PDB1
P1	GEB1/IO189PDB3
P2	GEB0/IO189NDB3
P3	VMV2
P4	IO179RSB2
P5	IO171RSB2
P6	IO165RSB2
P7	IO159RSB2
P8	IO151RSB2
P9	IO137RSB2
P10	IO134RSB2
P11	IO128RSB2
P12	VMV1
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO113NDB1
R1	GEA1/IO188PDB3
R2	GEA0/IO188NDB3
R3	IO184RSB2
R4	GEC2/IO185RSB2

FG484	
Pin Number	**AGL400 Function**
AA15	NC
AA16	NC
AA17	NC
AA18	NC
AA19	NC
AA20	NC
AA21	VCCIB1
AA22	GND
AB1	GND
AB2	GND
AB3	VCCIB2
AB4	NC
AB5	NC
AB6	IO121RSB2
AB7	IO119RSB2
AB8	IO114RSB2
AB9	IO109RSB2
AB10	NC
AB11	NC
AB12	IO104RSB2
AB13	IO103RSB2
AB14	NC
AB15	NC
AB16	IO91RSB2
AB17	IO90RSB2
AB18	NC
AB19	NC
AB20	VCCIB2
AB21	GND
AB22	GND
B1	GND
B2	VCCIB3
B3	NC
B4	NC
B5	NC
B6	NC

FG484	
Pin Number	**AGL400 Function**
U1	NC
U2	NC
U3	NC
U4	GEB1/IO136PDB3
U5	GEB0/IO136NDB3
U6	VMV2
U7	IO129RSB2
U8	IO128RSB2
U9	IO122RSB2
U10	IO115RSB2
U11	IO110RSB2
U12	IO98RSB2
U13	IO95RSB2
U14	IO88RSB2
U15	IO84RSB2
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO79VDB1
U20	NC
U21	NC
U22	NC
V1	NC
V2	NC
V3	GND
V4	GEA1/IO135PDB3
V5	GEA0/IO135NDB3
V6	IO127RSB2
V7	GEC2/IO132RSB2
V8	IO123RSB2
V9	IO118RSB2
V10	IO112RSB2
V11	IO106RSB2
V12	IO100RSB2
V13	IO96RSB2
V14	IO89RSB2

FG484	
Pin Number	**AGL1000 Function**
U1	IO195PDB3
U2	IO195NDB3
U3	IO194NPB3
U4	GEB1/IO189PDB3
U5	GEB0/IO189NDB3
U6	VMV2
U7	IO179RSB2
U8	IO171RSB2
U9	IO165RSB2
U10	IO159RSB2
U11	IO151RSB2
U12	IO137RSB2
U13	IO134RSB2
U14	IO128RSB2
U15	VMV1
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO113NDB1
U20	NC
U21	IO108NDB1
U22	IO109PDB1
V1	NC
V2	NC
V3	GND
V4	GEA1/IO188PDB3
V5	GEA0/IO188NDB3
V6	IO184RSB2
V7	GEC2/IO185RSB2
V8	IO168RSB2
V9	IO163RSB2
V10	IO157RSB2
V11	IO149RSB2
V12	IO143RSB2
V13	IO138RSB2
V14	IO131RSB2

Revision	Changes	Page
Revision 19 (continued)	The following sentence was removed from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry allows for rapid, single-voltage (3.3 V) programming of IGLOO devices via an IEEE 1532 JTAG interface" (SAR 28756).	1-3
	The "Specifying I/O States During Programming" section is new (SAR 21281).	1-8
	Values for VCCPLL at 1.2 V –1.5 V DC core supply voltage were revised in Table 2-2 • Recommended Operating Conditions 1 (SAR 22356). The value for VPUMP operation was changed from "0 to 3.45 V" to "0 to 3.6 V" (SAR 25220). The value for VCCPLL 1.5 V DC core supply voltage was changed from "1.4 to 1.6 V" to "1.425 to 1.575 V" (SAR 26551). The notes in the table were renumbered in order of their appearance in the table (SAR 21869).	2-2
	The temperature used in EQ 2 was revised from 110°C to 100°C for consistency with the limits given in Table 2-2 • Recommended Operating Conditions 1. The resulting maximum power allowed is thus 1.28 W. Formerly it was 1.71 W (SAR 26259).	2-6
	Values for CS196, CS281, and QN132 packages were added to Table 2-5 • Package Thermal Resistivities (SARs 26228, 32301).	2-6
	Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.425 V) and Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.14 V) were updated to remove the column for –20°C and shift the data over to correct columns (SAR 23041).	2-7
	The tables in the "Quiescent Supply Current" section were updated with revised notes on IDD (SAR 24112). Table 2-8 • Power Supply State per Mode is new.	2-7
	The formulas in the table notes for Table 2-41 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 21348).	2-37
	The row for 110°C was removed from Table 2-45 • Duration of Short Circuit Event before Failure. The example in the associated paragraph was changed from 110°C to 100°C. Table 2-46 • I/O Input Rise Time, Fall Time, and Related I/O Reliability1 was revised to change 110° to 100°C. (SAR 26259).	2-40
	The notes regarding drive strength in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section, "3.3 V LVCMOS Wide Range" section and "1.2 V LVCMOS Wide Range" section tables were revised for clarification. They now state that the minimum drive strength for the default software configuration when run in wide range is ±100 µA. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 25700).	2-28, 2-47, 2-77
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 24916): "It uses a 5 V–tolerant input buffer and push-pull output buffer."	2-56
	The values for $F_{DDRIMAX}$ and F_{DDOMAX} were updated in the tables in the "Input DDR Module" section and "Output DDR Module" section (SAR 23919).	2-94, 2-97
	The following notes were removed from Table 2-147 • Minimum and Maximum DC Input and Output Levels (SAR 29428): ±5% Differential input voltage = ±350 mV	2-81
	Table 2-189 • IGLOO CCC/PLL Specification and Table 2-190 • IGLOO CCC/PLL Specification were updated. A note was added to both tables indicating that when the CCC/PLL core is generated by Mircosemi core generator software, not all delay values of the specified delay increments are available (SAR 25705).	2-115

Revision / Version	Changes	Page
Revision 18 (Nov 2009)	The version changed to v2.0 for IGLOO datasheet chapters, indicating the datasheet contains information based on final characterization. Please review the datasheet carefully as most tables were updated with new data.	N/A
Revision 17 (Sep 2009) Product Brief v1.6	The "Reprogrammable Flash Technology" section was modified to add "250 MHz (1.5 V systems) and 160 MHz (1.2 V systems) System Performance."	I
	"IGLOO Ordering Information" was revised to note that halogen-free packages are available with RoHS-compliant packaging.	III
	Table 1-1 • I/O Standards Supported is new.	1-7
	The definitions of hot-swap and cold-sparing were added to the "I/Os with Advanced I/O Standards" section.	1-7
Revision 16 (Apr 2009) Product Brief v1.5	M1AGL400 is no longer offered and was removed from the "IGLOO Devices" product table, "IGLOO Ordering Information", and "Temperature Grade Offerings".	I, III, IV
	The –F speed grade is no longer offered for IGLOO devices. The speed grade column and note regarding –F speed grade were removed from "IGLOO Ordering Information". The "Speed Grade and Temperature Grade Matrix" section was removed.	III, IV
	This datasheet now has fully characterized data and has moved from being Advance to a Production version. The version number changed from Advance v0.5 to v2.0. Please review the datasheet carefully as most tables were updated with new data.	N/A
DC and Switching Characteristics Advance v0.6	3.3 V LVCMOS and 1.2 V LVCMOS Wide Range support was added to the datasheet. This affects all tables that contained 3.3 V LVCMOS and 1.2 V LVCMOS data.	
	I_{IL} and I_{IH} input leakage current information was added to all "Minimum and Maximum DC Input and Output Levels" tables.	N/A
	–F was removed from the datasheet. The speed grade is no longer supported.	N/A
	The notes in Table 2-2 • Recommended Operating Conditions 1 were updated.	2-2
	Table 2-4 • Overshoot and Undershoot Limits 1 was updated.	2-3
	Table 2-5 • Package Thermal Resistivities was updated.	2-6
	Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.425 V) and Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.14 V) were updated.	2-7
	In Table 2-191 • RAM4K9 and Table 2-193 • RAM4K9, the following specifications were removed: t_{WRO} t_{CCKH}	2-122 and 2-124
	In Table 2-192 • RAM512X18 and Table 2-194 • RAM512X18, the following specifications were removed: t_{WRO} t_{CCKH}	2-123 and 2-125
Revision 15 (Feb 2009) Packaging v1.9	The "QN132" pin table for the AGL060 device is new.	4-31